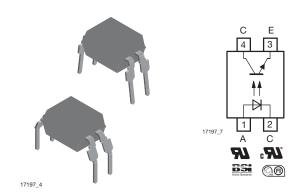
HS817, HS817G, HS817B, HS817BG

Vishay Semiconductors

Optocoupler with Transistor Output



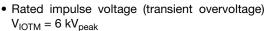
DESCRIPTION

The HS817 series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4-lead plastic dual inline package.

AGENCY APPROVALS

- BSI: EN 60065, EN 60950-1:2006
- FIMKO
- UL file no. E52744
- cUL tested to CSA 22.2 bulletin 5A

FEATURES





 Isolation test voltage (partial discharge test voltage) V_{pd} = 1.6 kV



Rated isolation voltage (RMS includes DC)
 V_{IOWM} = 600 V_{RMS}

RoHS COMPLIANT

- Rated recurring peak voltage (repetitive)
 V_{IORM} = 850 V_{peak}
- Creepage current resistance according to IEC 112, comparative tracking index: CTI ≥ 250
- Thickness through insulation ≥ 0.4 mm
- Isolation materials according to UL 94 V-O
- Pollution degree 2 (resp. IEC 664)
- Climatic classification 55/100/21 (IEC 68 part 1)
- Low temperature coefficient of CTR
- G = leadform 10.16 mm; provides creepage distance
 8 mm, suffix letter "G" is not marked on the optocoupler
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface

ORDERING INFORMATION						
H S 8	1 BER	7	CTR BIN	X PACKAGE OPTION	DIP-#	DIP-#, 400 mil
AGENCY CERTIFIED/PACKAGE			(CTR (%)		
UL, cUL, BSI, FIMKO		100 to 300			130 to 260	
DIP-4		HS817			HS817B	
DIP-4, 400 mil		HS817G			HS817BG	

Notes

- G = leadform 10.16 mm; G is not marked on the body.
- For additional information on the available options refer to option information.

HS817, HS817G, HS817B, HS817BG

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT					
INPUT									
Reverse voltage		V_{R}	6	V					
Forward current		I _F	60	mA					
Forward surge current	t _p ≤ 10 μs	I _{FSM}	1.5	Α					
Power dissipation	T _{amb} ≤ 25 °C	P _{diss}	100	mW					
Junction temperature		Tj	125	°C					
OUTPUT									
Collector emitter voltage		V _{CEO}	70	V					
Emitter collector voltage		V _{ECO}	7	V					
Collector current		Ic	50	mA					
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA					
Power dissipation	T _{amb} ≤ 25 °C	P _{diss}	150	mW					
Junction temperature		Tj	125	°C					
COUPLER									
Isolation test voltage (RMS)	t = 1 s	V _{ISO}	5	kV					
Total power dissipation	T _{amb} ≤ 25 °C	P _{tot}	250	mW					
Operating ambient temperature range		T _{amb}	- 40 to + 100	°C					
Storage temperature range		T _{stg}	- 55 to + 125	°C					
Soldering temperature (1)	2 mm from case, t ≤ 10 s	T _{sld}	260	°C					

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
 implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
 maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to wave profile for soldering conditions for through hole devices.

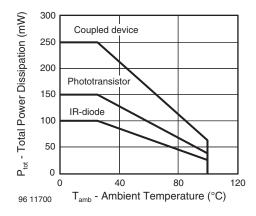


Fig. 1 - Total Power Dissipation vs. Ambient Temperature

HS817, HS817G, HS817B, HS817BG

Vishay Semiconductors

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	$I_F = 50 \text{ mA}$	V _F		1.43	1.6	V		
Junction capacitance	$V_R = 0 V$, $f = 1 MHz$	C _j		50		pF		
OUTPUT								
Collector emitter voltage	$I_C = 1 \text{ mA}$	V _{CEO}	70			V		
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7			V		
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0 \text{ A}$	I _{CEO}		10	100	nA		
COUPLER								
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V		
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA},$ $R_L = 100 \Omega$	f _c		110		kHz		
Coupling capacitance	f = 1 MHz	C _k		0.6		pF		

Note

Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering
evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART NUMBER	SYMBOL	MIN.	TYP.	MAX.	UNIT	
I _C /I _F	V _{CE} = 5 V, I _F = 5 mA	HS817	CTR	100		300	- %	
		HS817G	CTR	100		300		
		HS817B	CTR	130		260	70	
		HS817BG	CTR	130		260		

SAFETY AND INSULATION PARAMETERS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Insulation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω		
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹			Ω		
	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹			Ω		
Rated impulse voltage		V _{IOTM}			6	kV		
Max. working voltages	Recurring peak voltage	V _{IORM}	850			V _{peak}		
Forward current		I _{SI}			130	mA		
Power dissipation	T _{amb} ≤ 25 °C	P _{SO}			265	mW		
Safety temperature		T _{SI}			150	°C		
Creepage distance					7.6	mm		

Note

This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by
means of suitable protective circuits.



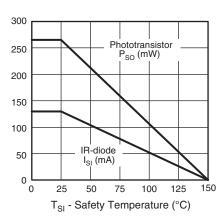


Fig. 2 - Derating Diagram

SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5$ V, $I_C = 2$ mA, $R_L = 100$ Ω , (see figure 3)	t _d		3		μs	
Rise time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$ (see figure 3)	t _r		3		μs	
Fall time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$ (see figure 3)	t _f		4.7		μs	
Storage time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$ (see figure 3)	t _s		0.3		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$ (see figure 3)	t _{on}		6		μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$ (see figure 3)	t _{off}		5		μs	
Turn-on time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$ (see figure 4)	t _{on}		2		μs	
Turn-off time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$ (see figure 4)	t _{off}		18		μs	

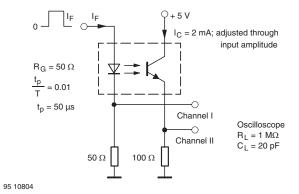


Fig. 3 - Test Circuit, Non-Saturated Operation

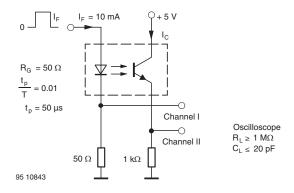


Fig. 4 - Test Circuit, Saturated Operation

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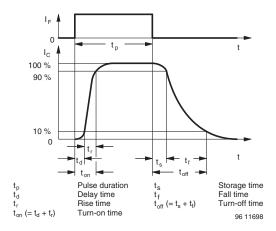


Fig. 5 - Switching Times

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

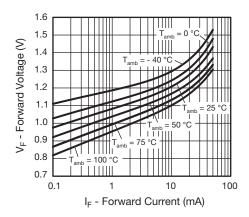


Fig. 6 - Forward Voltage vs. Forward Current

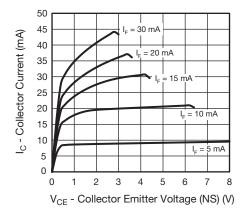


Fig. 7 - Collector Current vs. Collector Emitter Voltage (NS)

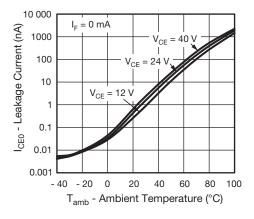


Fig. 8 - Leakage Current vs. Ambient Temperature

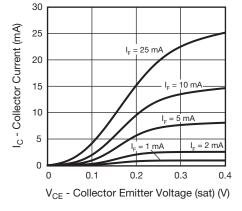


Fig. 9 - Collector Current vs. Collector Emitter Voltage (sat)

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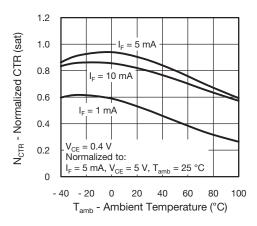


Fig. 10 - Normalized CTR (sat) vs. Ambient Temperature

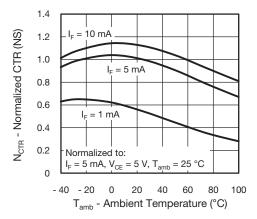


Fig. 11 - Normalized CTR (NS) vs. Ambient Temperature

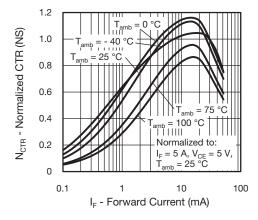


Fig. 12 - Normalized CTR (NS) vs. Forward Current

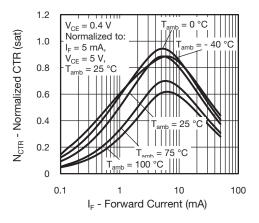


Fig. 13 - Normalized CTR (sat) vs. Forward Current

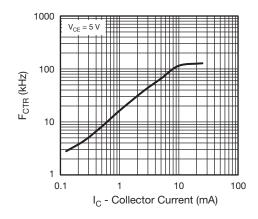


Fig. 14 - F_{CTR} vs. Collector Current

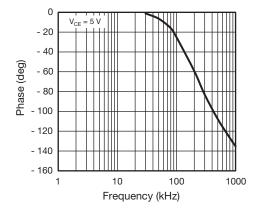


Fig. 15 - F_{CTR} vs. Phase Angle

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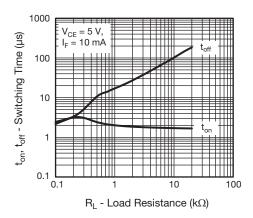
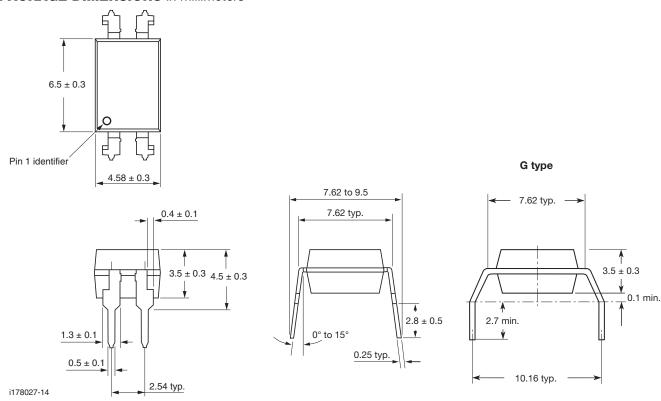
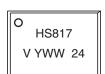


Fig. 16 - Switching Time vs. Load Resistance

PACKAGE DIMENSIONS in millimeters



PACKAGE MARKING (example)





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